

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions and listings of claims in the application.

### **LISTING OF CLAIMS**

1. (cancelled)
2. (cancelled)
3. (cancelled)
4. (cancelled)
5. (cancelled)
6. (cancelled)
7. (cancelled)
8. (cancelled)
9. (cancelled)
10. (cancelled)
11. (cancelled)
12. (cancelled)
13. (cancelled)
14. (cancelled)
15. (previously amended)      A method of manufacturing a circuit board

comprising:

the step of mounting a first component on a substrate by solder connection;

the step of arranging an anisotropic conductive film on a predetermined position

of the substrate;

the step of arranging a second component on the anisotropic conductive film;  
and  
the step of thermocompression-bonding the second component to said substrate  
with said anisotropic conductive film held therebetween;  
wherein said step of arranging said anisotropic conductive film on the  
predetermined position of said substrate is performed after said step of mounting the  
first component on said substrate by the solder connection.

16. (previously amended) A method of manufacturing a circuit board  
according to claim 15, wherein said step of mounting said first component on said  
substrate by the solder connection includes a reflow treatment.

17. (cancelled)

18. (cancelled)

19. (cancelled)

20. (cancelled)

21. (new) A method of manufacturing a circuit board in which components are  
mounted thereto, comprising:

a.) selecting a band region on a surface of the circuit board;

b.) soldering a first component onto the circuit board outside of the band  
region; and

c.) mounting a second component on the substrate within the band region  
with an anisotropic conductive film.

22. (new) The method of claim 21 where step c.) is performed with a heated  
compression bonding head, and

wherein the band region is selected to correspond generally to the areas over which the head travels during step c. ) thereby preventing impact of the head with the first components and isolating the first components from the heat generated by the head.

23. (new) The method of claim 22 wherein the first components are selected from the group of passive and mechanical components, and the second component is a semiconductor device.

24. (new) The method of claim 22 wherein the band region is wider than the head.

25. (new) The method of claim 22 wherein alignment marks are provided outside the band region.

26. (new) The method of claim 21 wherein step a.) is performed by a solder reflow process.

27. (new) The method of claim 21 wherein the band region divides a first set of first components on one part of the substrate and a second set of first components on a second part of the substrate.

28. (new) The method of claim 23 wherein the second components are selected from the group of a power source IC and a power source LSI.

29. (new) The method of claim 21 wherein the band region extends from one end of the substrate to another end of the substrate.

30. (new) The method of claim 21 wherein the band region extends rectilinearly along the substrate.

31. (new) The method of claim 21 which further comprises:  
forming wiring patterns on the substrate in the band region.
- 32, (new) The method of claim 21 which further comprises:  
forming a dummy electrode at a position associated with a second  
component.